

Silicon PNP Power Transistors

2SB860

DESCRIPTION

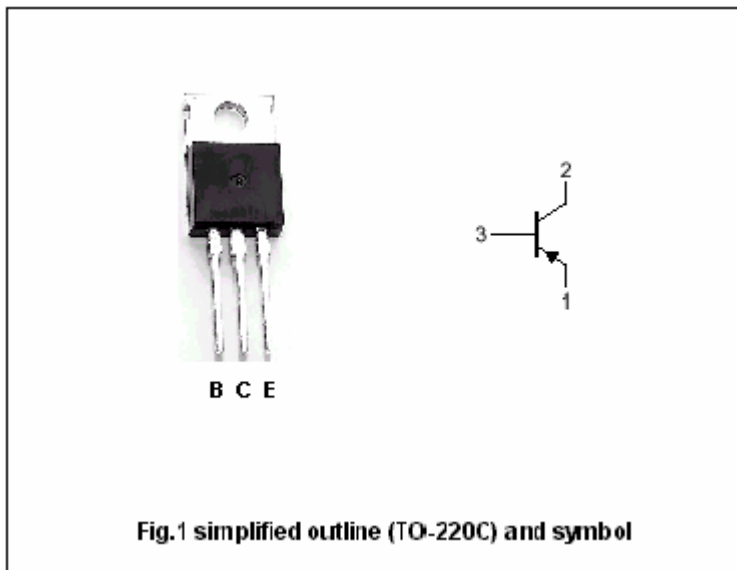
- With TO-220C package
- Complement to type 2SD1137

APPLICATIONS

- Low frequency power amplifier TV vertical deflection output applications

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base



Absolute maximum ratings(Ta=25)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	-100	V
V _{CEO}	Collector-emitter voltage	Open base	-100	V
V _{EBO}	Emitter-base voltage	Open collector	-4	V
I _C	Collector current		-4	A
I _{CP}	Collector current-Peak		-5	A
P _C	Collector power dissipation	T _a =25	1.8	W
		T _C =25	40	
T _j	Junction temperature		150	
T _{stg}	Storage temperature		-45~150	

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CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =-50mA; R _{BE} =	-100			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =-1mA; I _C =0	-4			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =-1 A; I _B =-0.1 A			-1.0	V
I _{CEO}	Collector cut-off current	V _{CE} =-80V; R _{BE} =			-100	μA
I _{EBO}	Collector cut-off current	V _{EB} =-3.5V; I _C =0			-50	μA
h _{FE-1}	DC current gain	I _C =-0.5A; V _{CE} =-4V	50		250	
h _{FE-2}	DC current gain	I _C =-50mA; V _{CE} =-4V	25		350	

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PACKAGE OUTLINE

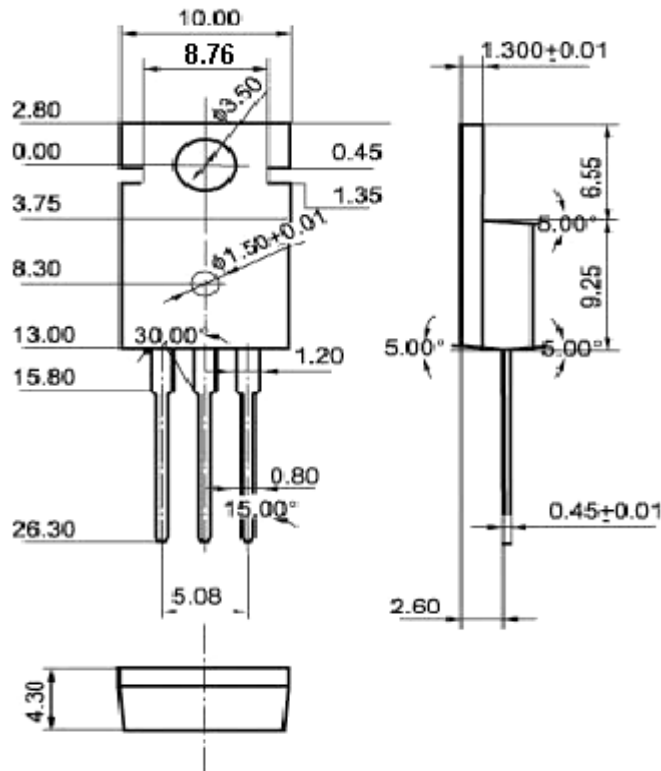


Fig.2 Outline dimensions (unindicated tolerance: ± 0.10 mm)

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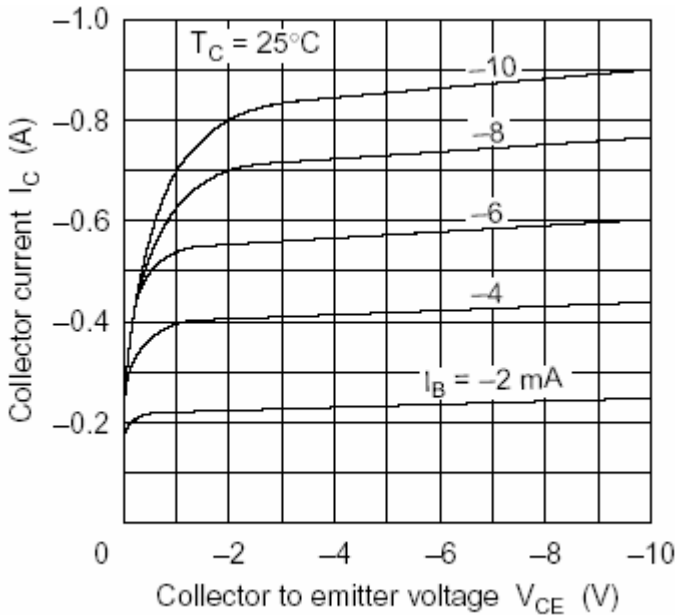


Fig.3 Static Characteristic

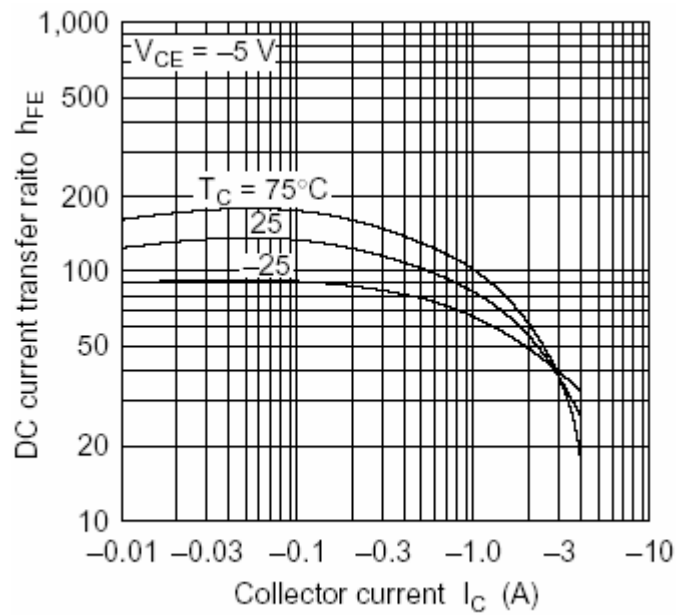


Fig.4 DC current Gain

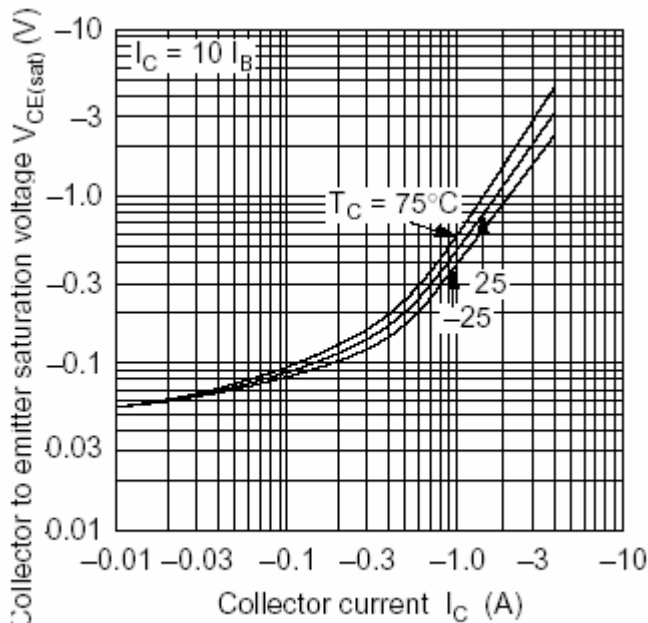


Fig.5 Collector-Emitter Saturation Voltage

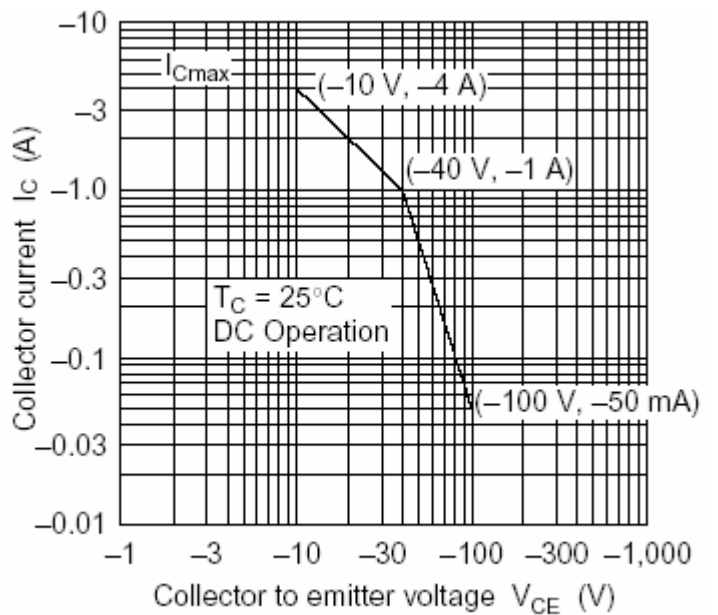


Fig.6 Safe Operating Area